

**DUAL 30V N-CHANNEL ENHANCEMENT MODE MOSFET
PowerDI3333-8 (Type UXC)**
Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
30V	20mΩ @ V _{GS} = 10V	32A
	32mΩ @ V _{GS} = 4.5V	25A

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

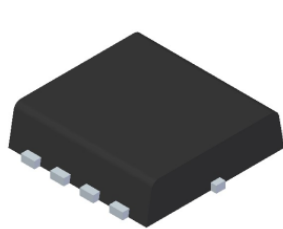
Applications

- Power Management Functions
- Analog Switch

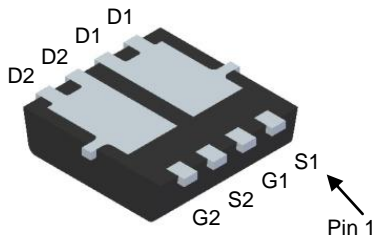
Mechanical Data

- Case: PowerDI[®] 3333-8 (Type UXC)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 Ⓢ
- Weight: 0.072 grams (Approximate)

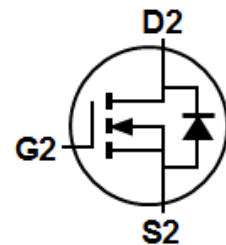
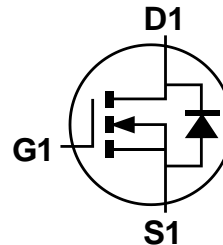
PowerDI3333-8 (Type UXC)



Top View



Bottom View

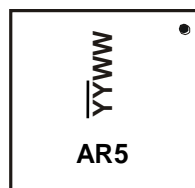


Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMT3020LDV-7	PowerDI3333-8 (Type UXC)	2,000/Tape & Reel
DMT3020LDV-13	PowerDI3333-8 (Type UXC)	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information


AR5 = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 18 for 2018)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V (Note 7)	Steady State	T _C = +25°C	I _D	32	A
		T _C = +70°C		25	
Maximum Body Diode Forward Current (Note 7)			I _S	25	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	50	A
Pulsed Drain Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I _{SM}	50	A
Avalanche Current (L = 0.1mH) (Note 8)			I _{AS}	13	A
Avalanche Energy (L = 0.1mH) (Note 8)			E _{AS}	8.5	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Total Power Dissipation (Note 5)			P _D	0.9	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		R _{θJA}	138	°C/W
Total Power Dissipation (Note 6)			P _D	1.9	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		R _{θJA}	67	°C/W
Thermal Resistance, Junction to Case (Note 7)			R _{θJC}	4.8	
Operating and Storage Temperature Range			T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV _{DSS}	30.0	—	—	V	V _{DS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1.0	µA	V _{DS} = 24V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(TH)}	1.0	—	2.5	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{D(S)ON}	—	14	20	mΩ	V _{GS} = 10V, I _D = 9.0A
			22	32		V _{GS} = 4.5V, I _D = 7.0A
Diode Forward Voltage	V _{SD}	—	8.0	1.2	V	V _{GS} = 0V, I _S = 2A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}	—	393	—	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	173	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	27	—	pF	
Gate Resistance	R _g	—	1.1	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 10V)	Q _g	—	7.0	—	nC	V _{DD} = 15V, I _D = 9A
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	3.6	—	nC	
Gate-Source Charge	Q _{gs}	—	0.9	—	nC	
Gate-Drain Charge	Q _{gd}	—	1.5	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	1.8	—	ns	
Turn-On Rise Time	t _r	—	1.9	—	ns	V _{DD} = 15V, V _{GS} = 10V, R _G = 6Ω, I _D = 9A
Turn-Off Delay Time	t _{D(OFF)}	—	7.5	—	ns	
Turn-Off Fall Time	t _f	—	2.4	—	ns	
Reverse Recovery Time	t _{RR}	—	10	—	ns	I _F = 9A, dI/dt = 100A/µs
Reverse Recovery Charge	Q _{RR}	—	2.6	—	nC	

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 9. Short duration pulse test used to minimize self-heating effect.
 10. Guaranteed by design. Not subject to product testing.

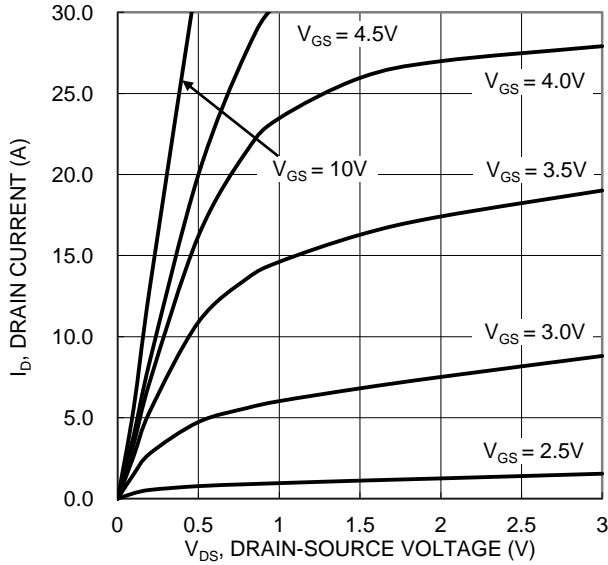


Figure 1. Typical Output Characteristic

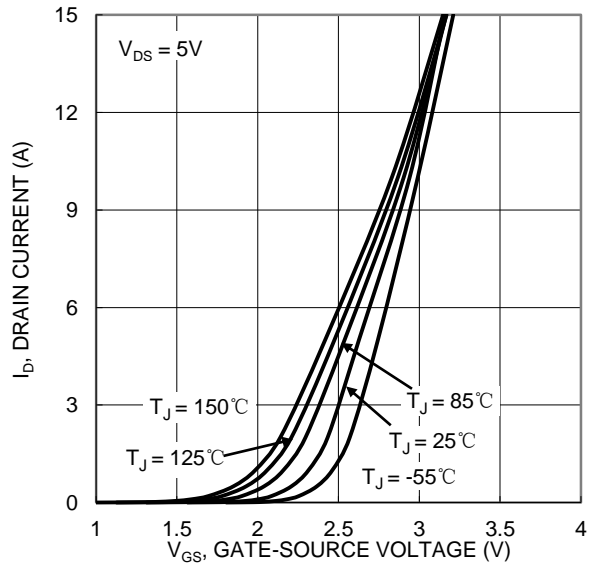


Figure 2. Typical Transfer Characteristic

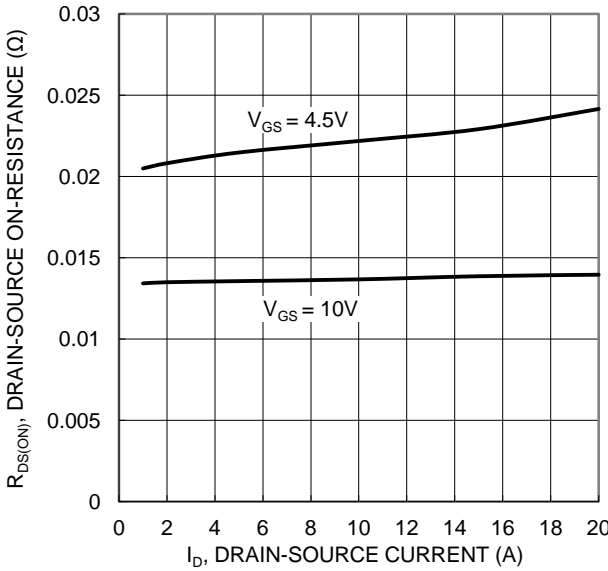


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

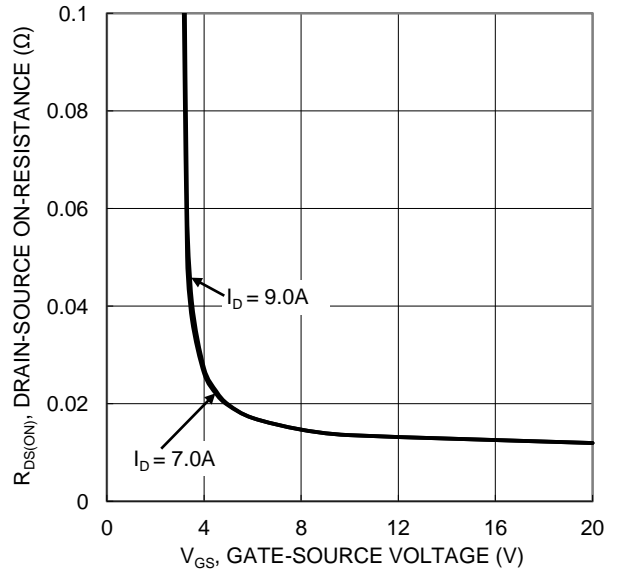


Figure 4. Typical Transfer Characteristic

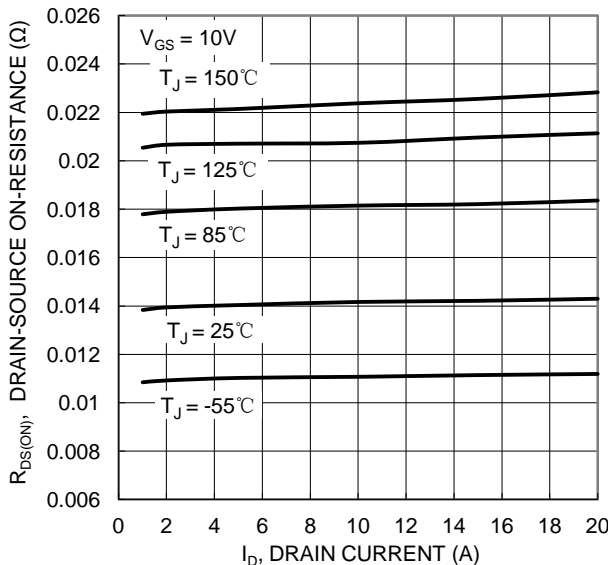


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

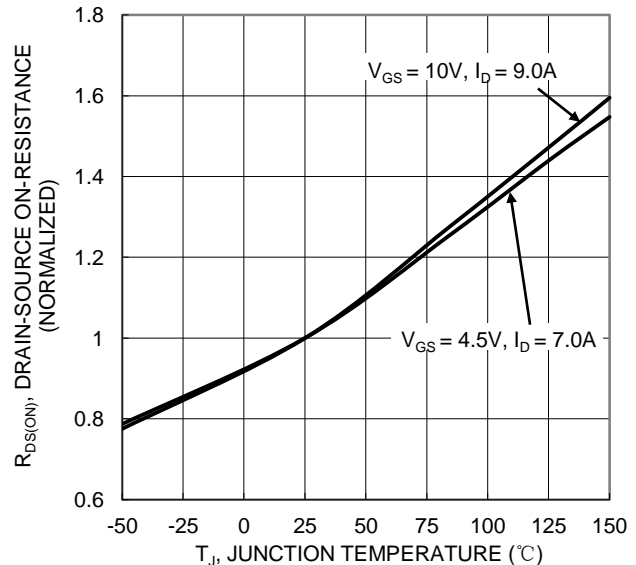


Figure 6. On-Resistance Variation with Junction Temperature

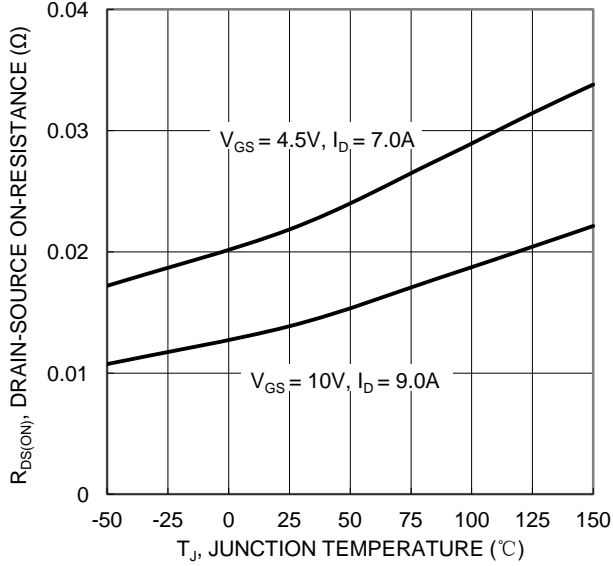


Figure 7. On-Resistance Variation with Junction Temperature

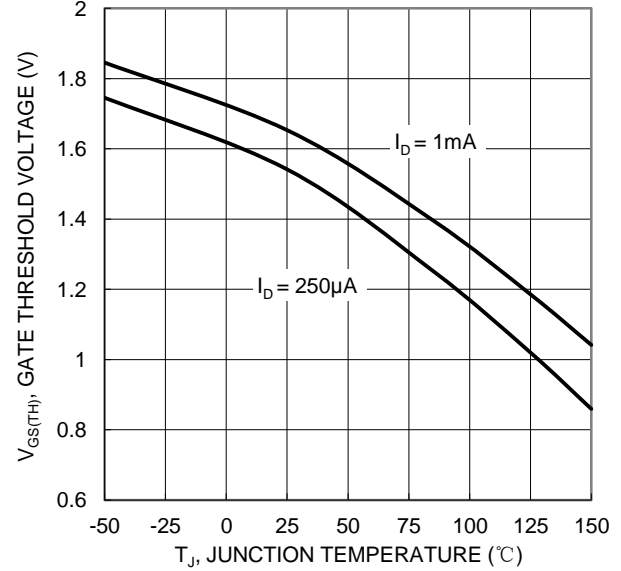


Figure 8. Gate Threshold Variation vs. Junction Temperature

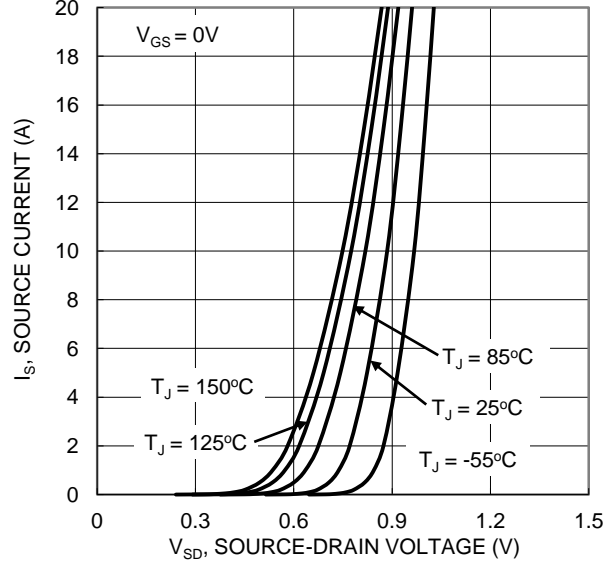


Figure 9. Diode Forward Voltage vs. Current

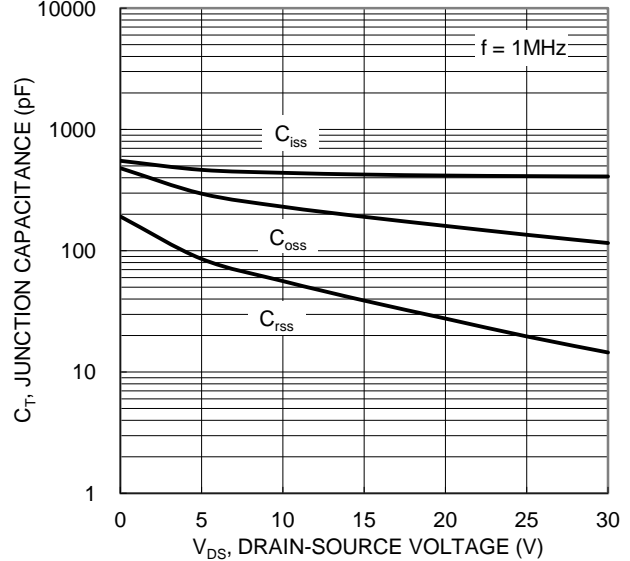


Figure 10. Typical Junction Capacitance

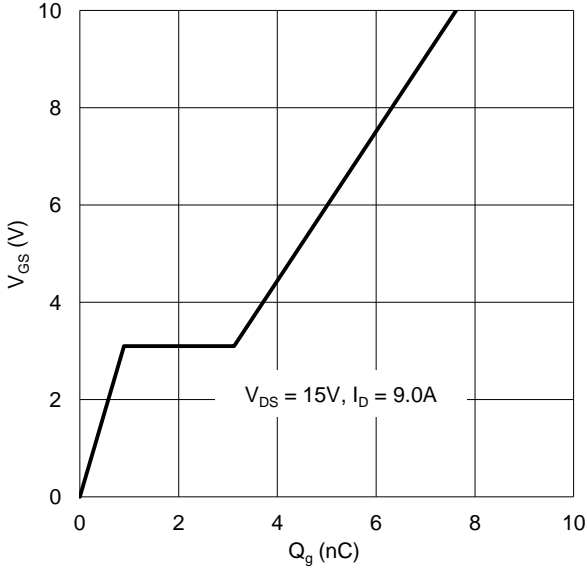


Figure 11. Gate Charge

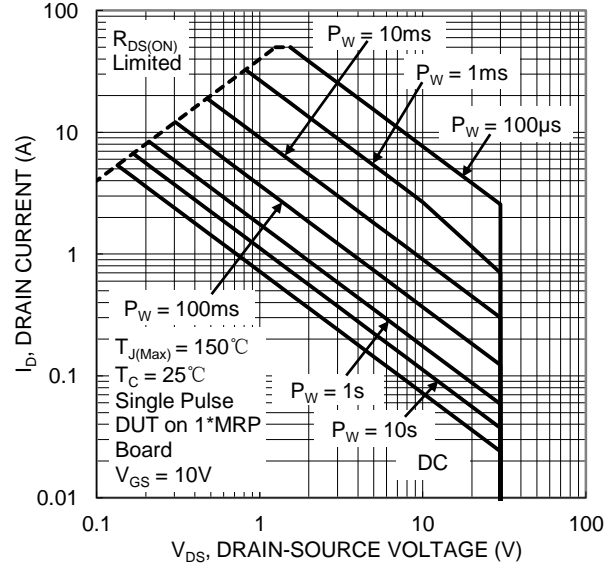


Figure 12. SOA, Safe Operation Area

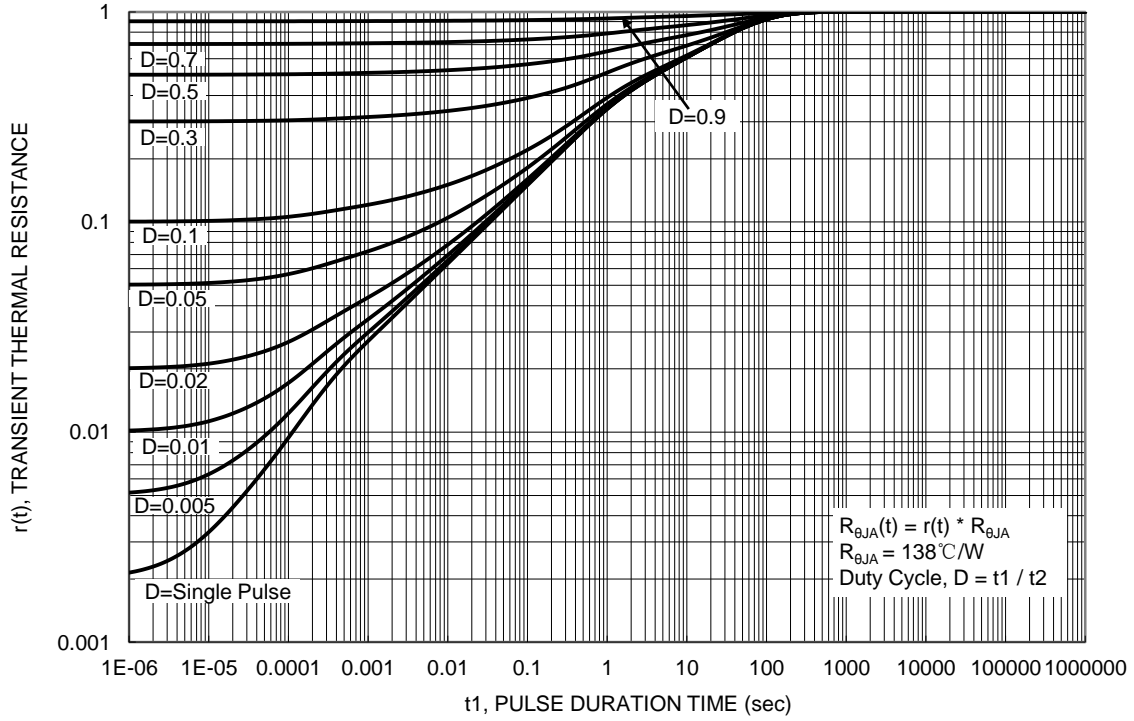
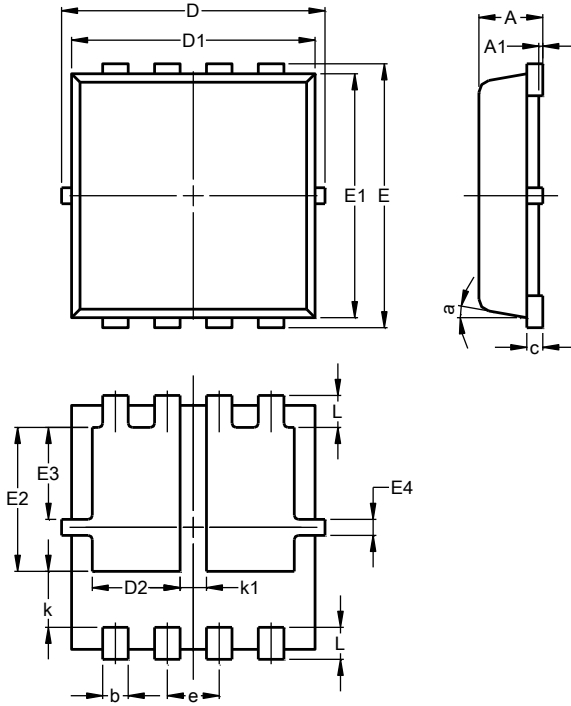


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8 (Type UXC)

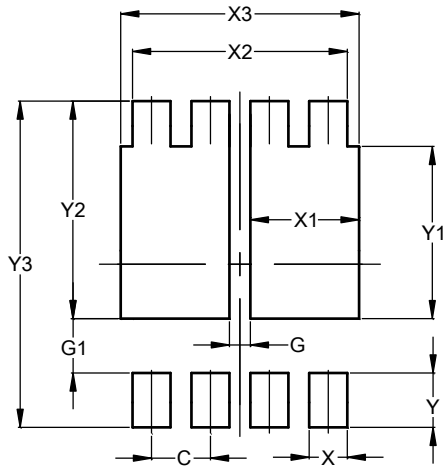


PowerDI3333-8 (Type UXC)			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	--
b	0.25	0.40	0.32
c	0.10	0.25	0.15
D	3.20	3.40	3.30
D1	2.95	3.15	3.05
D2	0.90	1.30	1.10
E	3.20	3.40	3.30
E1	2.95	3.15	3.05
E2	1.60	2.00	1.80
E3	0.95	1.35	1.15
E4	0.10	0.30	0.20
e	--	--	0.65
L	0.30	0.50	0.40
k	0.50	0.90	0.70
k1	0.13	0.53	0.33
a	0°	12°	10°
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8 (Type UXC)



Dimensions	Value (in mm)
C	0.650
G	0.230
G1	0.600
X	0.420
X1	1.200
X2	2.370
X3	2.630
Y	0.600
Y1	1.900
Y2	2.400
Y3	3.600

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- Техническая поддержка проекта;
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